

AMENDMENTS TO THE SPECIFICATION

IN THE ABSTRACT OF THE DISCLOSURE:

Replace the Abstract of the Disclosure currently of record with the attached new Abstract of the Disclosure.

IN THE SPECIFICATION:

Please amend paragraph [0012] as follows:

[0012] In one embodiment, ~~the first~~ a third voltage is applied to the first conductivity type semiconductor substrate, the first conductivity type well region provided in the semiconductor substrate, or the first conductivity type semiconductor film disposed on the insulator.

Please amend paragraph [0014] as follows:

[0014] In one embodiment, the first conductivity type is P type,
the second conductivity type is N type,
the carriers are positive holes,
the first voltage is higher than the reference voltage, and
the second voltage is lower than the reference voltage, and
the third voltage is higher than the reference voltage.

Please amend paragraph [0017] as follows:

[0017] In one embodiment, the first conductivity type is N type,

the second conductivity type is P type,
the carriers are electrons,
the first voltage is lower than the reference voltage, and
the second voltage is higher than the reference voltage-, and
the third voltage is lower than the reference voltage.

Please amend paragraph [0022] as follows:

[0022] In one embodiment, an absolute value of voltage difference between ~~the other of~~
~~the second conductivity type diffusion layer regions, and, the first conductivity type~~
~~semiconductor substrate, the first conductivity type well region provided in the semiconductor~~
~~substrate or the first conductivity type semiconductor film disposed on the insulator~~ the second
voltage and third voltage is 0.7V or more and 1V or less.